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(54) Title: THIN-FILM TRANSISTORS WITH GATE-SOURCE CAPACITANCE TUNING

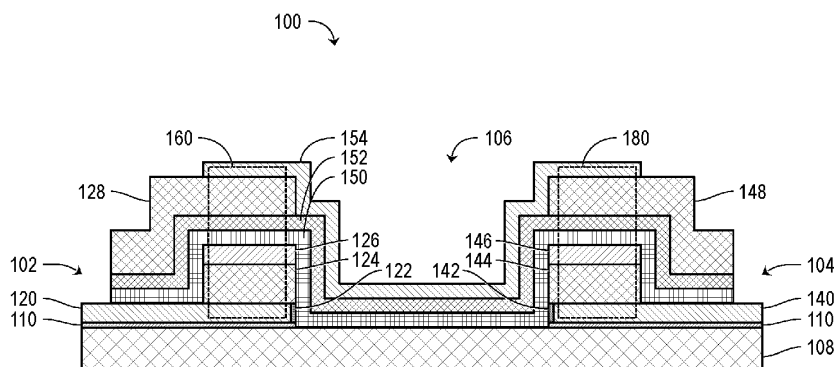


FIG. 1

(57) Abstract: An example thin-film transistor includes a source and a gate. The source includes a body of source metal and a body of capacitance-tuning material disposed on the body of source metal. The body of capacitance-tuning material is configured to control a capacitance between the source and the gate. A drain of the thin-film transistor may also include a body of capacitance-tuning material. Capacitance-tuning material may be provided outside the source/drain, for example, adjacent a gate dielectric material. The thin-film transistor may further include a body of reducing material to draw oxygen out of other materials of the thin-film transistor. The thin-film transistor may further include a body of hardmask material used during the making of the thin-film transistor.

[Continued on next page]

WO 2025/163584 A1

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